

31. (Amended) A method according to claim 30, wherein said octamethylcyclotetrasiloxane increases deposition efficiency, defined as a function of grams of SiO₂ produced at the combustion burner, over that achieved when silicon tetrachloride is utilized as a silicon-containing compound in vapor form.

32. (Amended) A method according to claim 31, wherein the deposition efficiency, defined as a function of grams of SiO₂ produced at the combustion burner, increase is about 20%.

REMARKS

In view of the above amendments and the following remarks, reconsideration of the outstanding office action is respectfully requested.

Of the patent claims, claims 1 and 4-26 are pending, while claims 2-3 and 24-25 are cancelled. Added claims 27-32 are pending. The status of the pending claims is that claims 1, 4-23, 26-27, and 30 are allowed and claims 28-29 and 31-32 stand rejected.

The objection to the application under 35 U.S.C. § 251 as lacking written consent of all assignees is respectfully traversed in view of the attached Supplemental Statement by Assignee in Support of Reissue. Further, pursuant to 35 U.S.C. § 251, applicants hereby surrender U.S. Patent No. 5,043,002. See attached Surrender of U.S. Patent No. 5,043,002.

The objection to the declaration and the rejection of claims 1, 4-23, and 26-31 under 35 U.S.C. § 251 is respectfully traversed in view of the attached Supplemental Combined Declaration and Power of Attorney form.

The rejection of claims 28-29 and 31-32 under 35 U.S.C. § 112 (2nd para.) as indefinite is respectfully traversed in view of the above amendments. More particularly, in each of these claims, the phrase "defined as a function of grams of SiO₂ produced at the combustion burner," is inserted after the word "efficiency." Support for these amendments is found in Figure 4 of U.S. Patent No. 5,043,002.

The rejection of claims 28-29 and 31-32 under 35 U.S.C. § 112 (1st para.) for lack of enablement is respectfully traversed. Although claim 23 requires a halide-free polymethylcyclsiloxane, it is not inconsistent with the limitations of claims 28-29 and 31-32. More particularly, the latter claims do not require use of silicone tetrachloride; they

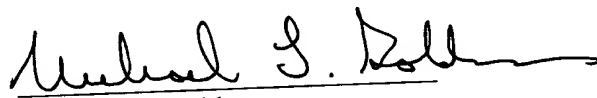
simply define the deposition efficiency of the claimed halide-free method in comparison with the deposition efficiency of a method utilizing silicone tetrachloride. To better emphasize this, claims 28 and 31 have been amended so that "said silicon-containing compound in vapor form" is replaced with "a silicon-containing compound in vapor form". This distinguishes silicon tetrachloride from the silicon-containing compound of claims 1 and 23.

Applicants have resubmitted the previously-filed PTO-1449 form with complete information about the cited references. Therefore, it is respectfully requested that the cited references be considered and that the PTO-1449 form be initialed by the U.S. Patent and Trademark Office to indicate such consideration.

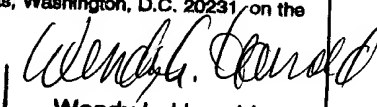
In view of all the foregoing comments, it is respectfully submitted that this case is in condition for allowance and such allowance is earnestly solicited.

Respectfully submitted,

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I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on the date below.	
6/3/98 Date	 Wendy L. Harrold